

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Eliyahou Harari
Title: Flash Memory Cell Arrays Having Dual Control Gates Per Memory Cell Charge Storage Element
Application No.: Unassigned Filing Date: Herewith
Examiner: Unassigned Group Art Unit: Unassigned
Docket No.: SNDK.304US1 Conf. No.: Unassigned

Mail Stop Patent Application
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Dear Sir:

Pursuant to 37 C.F.R. §§ 1.56, 1.97 and 1.98, Applicant calls the documents listed on the enclosed Form PTO-1449 to the Examiner's attention in this patent application. Copies of the documents listed on the accompanying Form PTO-1449 and Form PTO-892 that are not enclosed were previously submitted in Application No. 10/282,747 from which this Application claims an earlier effective filing date.

Citation of these documents shall not be construed as (1) an admission that the documents are prior art with respect to the invention or inventions claimed in this application, (2) a representation that a search has been made (other than as indicated by any cited document), or (3) an admission that the cited information is, or is considered to be, material to patentability as defined in § 1.56(b).

Attorney Docket No.: SNDK.304US1
Express Mail No.: EV321705732US

Application No.: Unassigned

This information disclosure statement is submitted under 37 C.F.R. § 1.97(b) and consequently no fee should be required. The Commissioner is authorized, however, to charge any fee that may be required, or to credit any overpayment, against Deposit Account No. 502664. This form is being submitted in duplicate.

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EV321705732US

Respectfully submitted,



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March 1, 2004

Date

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Attorney Docket No.: SNDK.304US1
Express Mail No.: EV321705732US

Application No.: Unassigned

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Eliyahou Harari

COPY

Assignee: SanDisk Corporation

Title: Flash Memory Cell Arrays Having Dual Control Gates Per Memory Cell Charge Storage Element

Application No.: 10/282,747 Filing Date: October 28, 2002

Examiner: Unassigned Group Art Unit: 2811

Docket No.: M-12879 US Conf. No.: 7200

San Francisco, California
January 14, 2003

Box Missing Parts
Commissioner for Patents
Washington, D. C. 20231

**INFORMATION DISCLOSURE STATEMENT
UNDER 37 CFR § 1.97(b)**

Dear Sir:

Pursuant to 37 C.F.R. § 1.56, § 1.97 and § 1.98, the documents listed on the accompanying form PTO-1449 are called to the attention of the Examiner for the above patent application. Copies of these documents are enclosed.

Citation of these documents shall not be construed as:

1. an admission that the documents are necessarily prior art with respect to the instant invention;
2. a representation that a search has been made; or
3. an admission that the information cited herein is, or is considered to be, material to patentability as defined in § 1.56(b).

EXPRESS MAIL LABEL NO:

EV259164530US

Respectfully submitted,

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| U.S. Department of Commerce, Patent and Trademark Office | | Atty Docket No. | Application No. |
| | | M-12879 US | 10/282,747 |
| INFORMATION DISCLOSURE STATEMENT BY APPLICANT | | Applicant | |
| (Use several sheets if necessary) | | Eliyahou Harari | |
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| U.S. Department of Commerce, Patent and Trademark Office | | Atty Docket No. | Application No. |
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Express Mail No.: EV259164530US

Notice of References Cited**COPY**

Application/Control No.

10/282,747

Applicant(s)/Patent Under

Reexamination

HARARI, ELIYAHOU

Examiner

Viet Q Nguyen

Art Unit

2818

Page 1 of 1

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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)

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